

## SOT-23 Formed SMD Package

BCX17  
BCX18

## SILICON PLANAR EPITAXIAL TRANSISTORS

*P-N-P transistors*

### Marking

BCX17 = T1

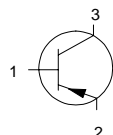
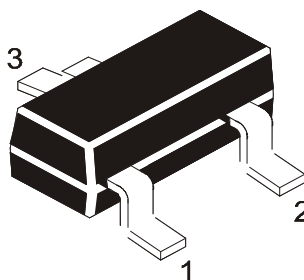
BCX18 = T2

### Pin configuration

1 = BASE

2 = EMITTER

3 = COLLECTOR



### ABSOLUTE MAXIMUM RATINGS

		BCX17	BCX18
Collector-emitter voltage ( $V_{BE} = 0$ )	$-V_{CES}$ max.	50	30 V
Collector-emitter voltage (open base)	$-V_{CE0}$ max.	45	25 V
Collector current (peak value)	$-I_{CM}$ max.	1000	mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	$P_{tot}$ max.	250	mW
Junction temperature	$T_j$ max.	150	$^{\circ}\text{C}$
D.C. current gain			
$-I_C = 100\text{ mA}; -V_{CE} = 1\text{ V}$	$h_{FE}$	100 to 600	
Transition frequency			
$-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}; f = 35\text{ MHz}$	$f_T$ typ.	100	MHz

# BCX17 BCX18

**RATINGS** (at  $T_A = 25^\circ\text{C}$  unless otherwise specified)

Limiting values

		<b>BCX17</b>	<b>BCX18</b>
Collector-emitter voltage ( $V_{BE} = 0$ )	$-V_{CES}$ max.	50	30 V
Collector-emitter voltage $-I_C = 10$ mA (see Fig. 2)	$-V_{CE0}$ max.	45	25 V
Emitter-base voltage (open collector)	$-V_{EB0}$ max.	5	5 V
Collector current (d.c.)	$-I_C$ max.	500	mA
Collector current (peak value)	$-I_{CM}$ max.	1000	mA
Emitter current (peak value)	$I_{EM}$ max.	1000	mA
Base current (d.c.)	$-I_B$ max.	100	mA
Base current (peak value)	$-I_{BM}$ max.	200	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}^*$	$P_{tot}$ max.	250	mW
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Junction temperature	$T_j$ max.	150	$^\circ\text{C}$

## THERMAL RESISTANCE

From junction to ambient

$$R_{th\ j-a} = 500\ \text{K/W}$$

## CHARACTERISTICS

$T_j = 25^\circ\text{C}$  unless otherwise specified

Collector cut-off current

$I_E = 0$ ;  $-V_{CB} = 20$  V

$$-I_{CB0} < 100\ \text{nA}$$

$I_E = 0$ ;  $-V_{CB} = 20$  V;  $T_j = 150^\circ\text{C}$

$$-I_{CB0} < 5\ \mu\text{A}$$

Emitter cut-off current

$I_C = 0$ ;  $-V_{EB} = 5$  V

$$-I_{EB0} < 10\ \mu\text{A}$$

Base-emitter voltage

$-I_C = 500$  mA;  $-V_{CE} = 1$  V

$$-V_{BE} < 1,2\ \text{V}$$

Saturation voltage

$-I_C = 500$  mA;  $-I_B = 50$  mA

$$-V_{CEsat} < 620\ \text{mV}$$

D.C. current gain

$-I_C = 100$  mA;  $-V_{CE} = 1$  V

$$h_{FE} 100\ \text{to}\ 600$$

$-I_C = 300$  mA;  $-V_{CE} = 1$  V

$$h_{FE} > 70$$

$-I_C = 500$  mA;  $-V_{CE} = 1$  V

$$h_{FE} > 40$$

Transition frequency at  $f = 35$  MHz

$-I_C = 10$  mA;  $-V_{CE} = 5$  V

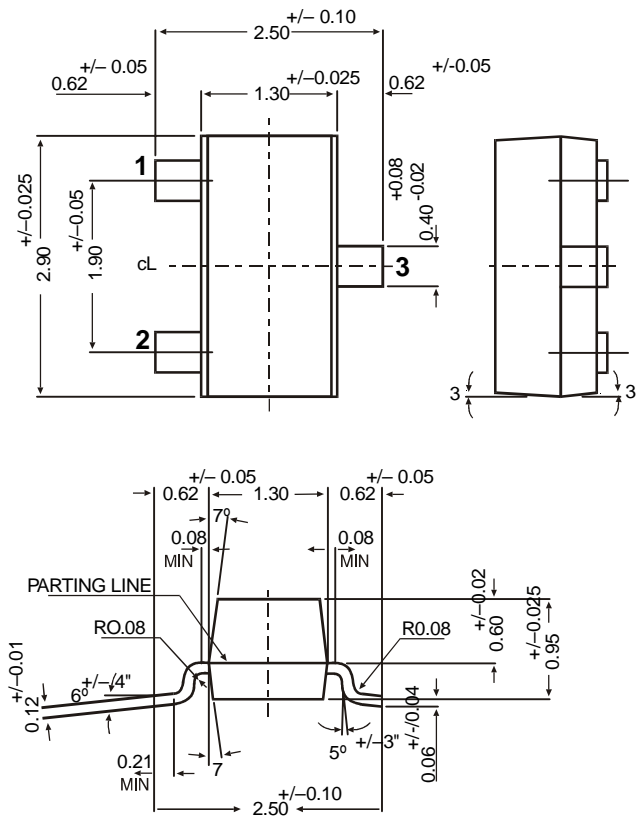
$$f_T\ \text{typ.}\ 100\ \text{MHz}$$

Collector capacitance at  $f = 1$  MHz

$I_E = I_e = 0$ ;  $-V_{CB} = 10$  V

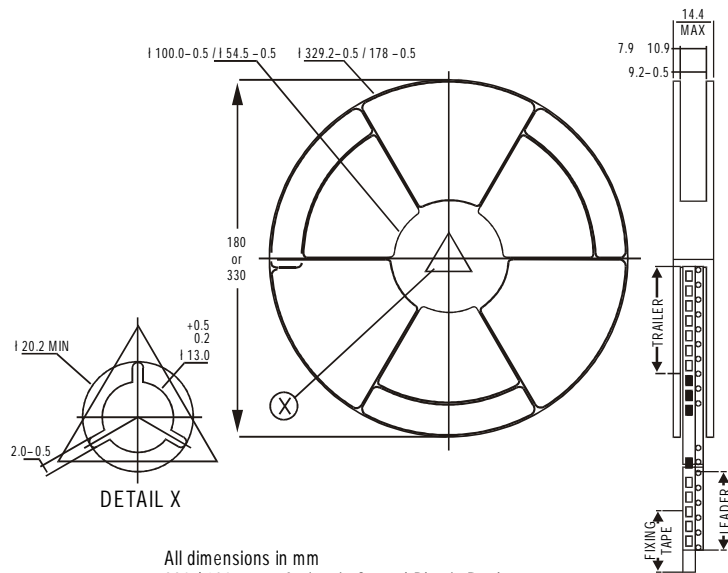
$$C_c\ \text{typ.}\ 8\ \text{pF}$$

## SOT-23 Formed SMD Package



## SOT-23 Package Reel Information

### Reel specifications for Packing (13"/7" reels)



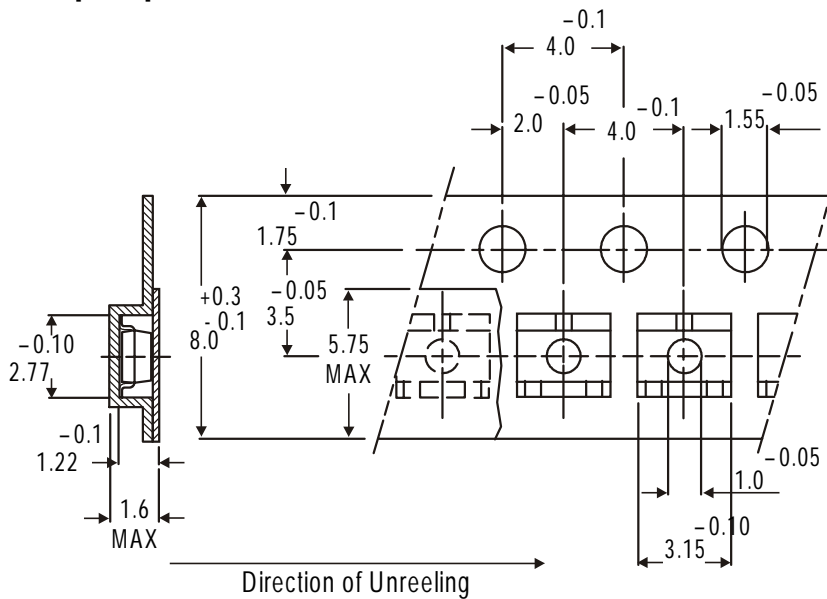
All dimensions in mm  
330 / 180 mm Antistatic Coated Plastic Reel

NOTES:

	8mm Tape	8mm Tape
	Size of Reel	Size of Reel
	330 mm (13")	180 mm (7")
No. of Devices	10,000 Pcs	3,000 Pcs

1. The bandolier of 330 mm reel contains at least 10,000 devices.
2. The bandolier of 180 mm reel contains at least 3,000 devices.
3. No more than 0.5% missing devices / reel. 50 empty compartments for 330 mm reel. 15 empty compartments for 180 mm reel.
4. Three consecutive empty places might be found provided this gap is followed by 6 consecutive devices.
5. The carrier tape (leader) starts with at least 75 empty positions (equivalent to 330 mm). In order to fix the carrier tape a self adhesive tape of 20 to 50 mm is applied. At the end of the bandolier at least 40 empty positions (equivalent to 160 mm) are there.

## Tape Specification for SOT-23 Surface Mount Device



**All dimensions in mm**

## Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
SOT-23 T&R	3K/reel	136 gm/3K pcs	3" x 7.5" x 7.5"	12.0K	17" x 15" x 13.5"	192.0K	12 kgs
			9" x 9" x 9"	51.0K	19" x 19" x 19"	408.0K	28 kgs
	10K/reel	415 gm/10K pcs	13" x 13" x 0.5"	10.0K	17" x 15" x 13.5"	300.0K	16 kgs

## Customer Notes

### Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

## Disclaimer

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